R8005ANX

Nch 800V 5A Power MOSFET

Datasheet

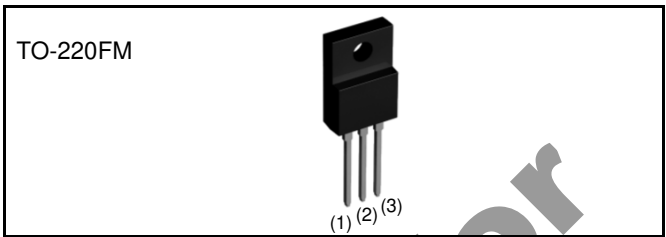|	
V_{DSS}	800V
$R_{DS(on)}$ (Max.)	2.08Ω
I_D	5A
P_D	51W

● **Features**

1) Low on-resistance.

2) Fast switching speed.

3) Gate-source voltage (V_{GSS}) guaranteed to be ±30V.

4) Drive circuits can be simple.

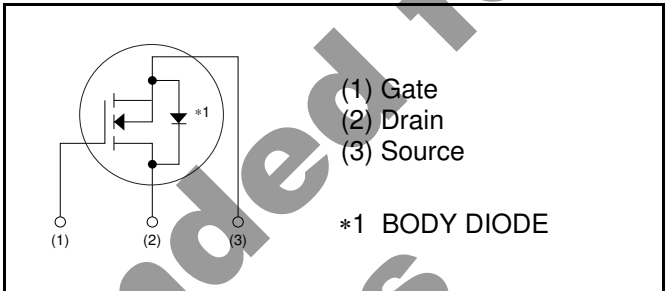5) Parallel use is easy.

6) Pb-free lead plating ; RoHS compliant

● **Application**

Switching Power Supply

● **Outline**

TO-220FM

● **Inner circuit**

(1) Gate
(2) Drain
(3) Source

∗1 BODY DIODE

● **Packaging specifications**

Type	Packaging	Bulk
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	R8005ANX

● **Absolute maximum ratings**(T_a = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	800	V
Continuous drain current	T_c = 25°C	I_D [*1]	±5	A
	T_c = 100°C	I_D [*1]	±2.4	A
Pulsed drain current		$I_{D,pulse}$ [*2]	±20	A
Gate - Source voltage		V_{GSS}	±30	V
Avalanche energy, single pulse		E_{AS} [*3]	1.66	mJ
Avalanche energy, repetitive		E_{AR} [*4]	1.3	mJ
Avalanche current		I_{AR} [*3]	2.5	A
Power dissipation (T_c = 25°C)		P_D	51	W
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	−55 to +150	°C
Reverse diode dv/dt		dv/dt [*5]	15	V/ns

● Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	V_{DS} = 640V, I_D = 5A T_j = 125°C	50	V/ns

● Thermal resistance

Parameter	Symbol	Values Min.	Values Typ.	Values Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.41	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

● Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values Min.	Values Typ.	Values Max.	Unit
Drain - Source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	800	-	-	V
Drain - Source avalanche breakdown voltage	$V_{(BR)DS}$	V_{GS} = 0V, I_D = 2.5A	-	900	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} = 800V, V_{GS} = 0V T_j = 25°C	-	0.1	100	μA
		T_j = 125°C	-	-	1000	
Gate - Source leakage current	I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = 10V, I_D = 1mA	3	-	5	V
Static drain - source on - state resistance	$R_{DS(on)}$ [6]	V_{GS} = 10V, I_D = 2.5A T_j = 25°C	-	1.60	2.08	Ω
		T_j = 125°C	-	3.69	-	
Gate input resistance	R_G	f = 1MHz, open drain	-	7.7	-	Ω

●Electrical characteristics(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Transconductance	g_{fs} [*6]	V_{DS} = 10V, I_D = 2.5A	1	2	-	S
Input capacitance	C_{iss}	V_{GS} = 0V	-	485	-	pF
Output capacitance	C_{oss}	V_{DS} = 25V	-	250	-	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	21	-	
Effective output capacitance, energy related	$C_{o(er)}$	V_{GS} = 0V V_{DS} = 0V to 640V	-	16.8	-	pF
Effective output capacitance, time related	$C_{o(tr)}$		-	41.2	-	
Turn - on delay time	$t_{d(on)}$ [*6]	$V_{DD} \simeq$ 400V, V_{GS} = 10V	-	17	-	ns
Rise time	t_r [*6]	I_D = 2.5A	-	17	-	
Turn - off delay time	$t_{d(off)}$ [*6]	R_L = 160Ω	-	37	74	
Fall time	t_f [*6]	R_G = 10Ω	-	41	82	

●Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g [*6]	$V_{DD} \simeq$ 400V	-	21	-	nC
Gate - Source charge	Q_{gs} [*6]	I_D = 5A	-	4.4	-	
Gate - Drain charge	Q_{gd} [*6]	V_{GS} = 10V	-	11	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \simeq$ 400V, I_D = 5A	-	7.4	-	V

*1 Limited only by maximum temperature allowed.

*2 $P_W \leq$ 10μs, Duty cycle ≤ 1%

*3 L ≃ 500μH, V_{DD} = 50V, R_G = 25Ω, starting T_j = 25°C

*4 L ≃ 500μH, V_{DD} = 50V, R_G = 25Ω, starting T_j = 25°C, f = 10kHz

*5 Reference measurement circuits Fig.5-1.

*6 Pulsed

● **Body diode electrical characteristics** (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Inverse diode continuous, forward current	I_S [*1]	T_c = 25°C	-	-	5	A
Inverse diode direct current, pulsed	I_{SM} [*2]		-	-	20	A
Forward voltage	V_{SD} [*6]	V_{GS} = 0V, I_S = 5A	-	-	1.5	V
Reverse recovery time	t_{rr} [*6]	I_S = 5A di/dt = 100A/µs	-	554	-	ns
Reverse recovery charge	Q_{rr} [*6]		-	4.6	-	µC
Peak reverse recovery current	I_{rrm} [*6]		-	16.5	-	A
Peak rate of fall of reverse recovery current	di_{rr}/dt	T_j = 25°C	-	30	-	A/µs

● **Typical Transient Thermal Characteristics**

Symbol	Value	Unit		Symbol	Value	Unit
R_{th1}	0.258			C_{th1}	0.00169	
R_{th2}	0.966	K/W		C_{th2}	0.0194	Ws/K
R_{th3}	2.18			C_{th3}	0.461	

● **Electrical characteristic curves**

Fig.1 Power Dissipation Derating Curve

Fig.2 Maximum Safe Operating Area

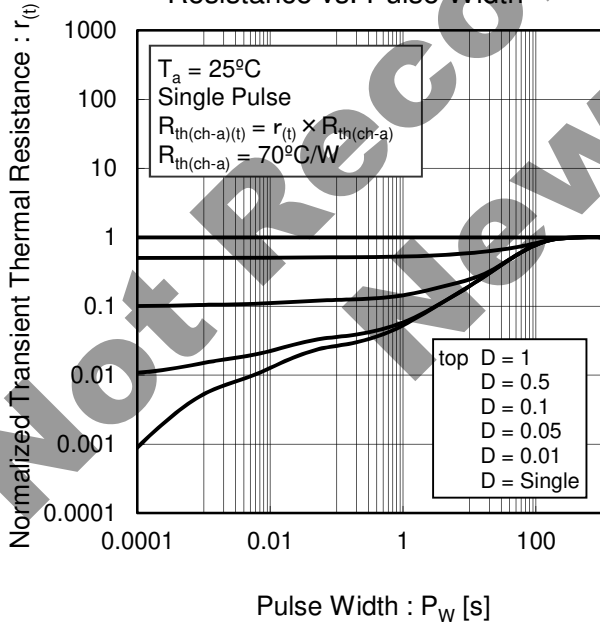Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

$T_a = 25°C$
Single Pulse
$R_{th(ch-a)(t)} = r_{(t)} \times R_{th(ch-a)}$
$R_{th(ch-a)} = 70°C/W$

top D = 1
D = 0.5
D = 0.1
D = 0.05
D = 0.01
D = Single

● **Electrical characteristic curves**

Fig.4 Avalanche Current vs Inductive Load

Fig.5 Avalanche Power Losses

Fig.6 Avalanche Energy Derating Curve
     vs Junction Temperature

● **Electrical characteristic curves**

Fig.7 Typical Output Characteristics(I)
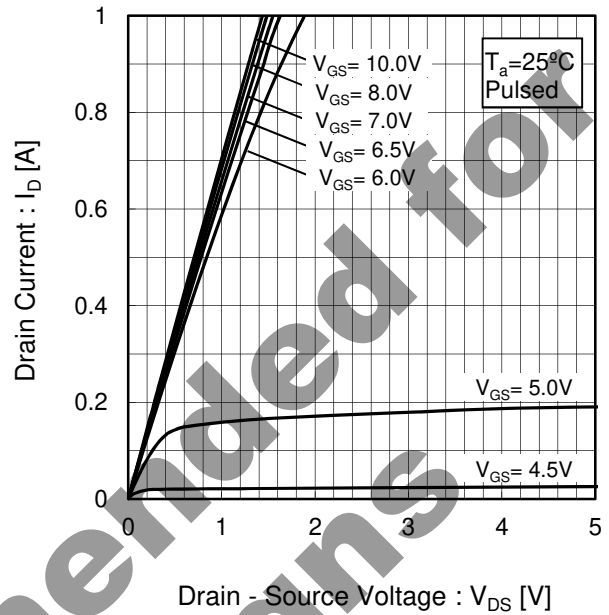

Fig.8 Typical Output Characteristics(II)

Fig.9 T$_j$ = 150°C Typical Output Characteristics(I)

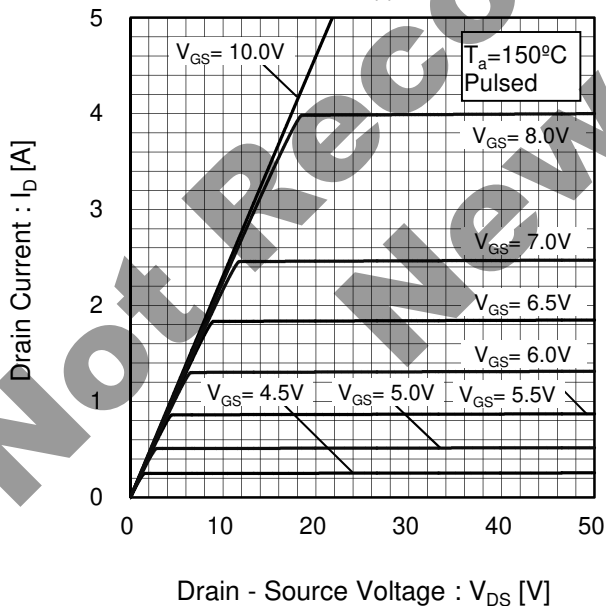Fig.10 T$_j$ = 150°C Typical Output Characteristics(II)

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● **Electrical characteristic curves**

Fig.11 Breakdown Voltage
vs. Junction Temperature
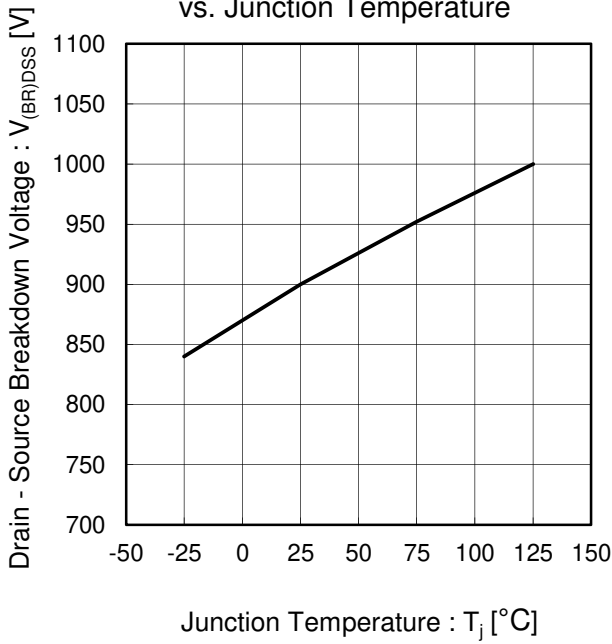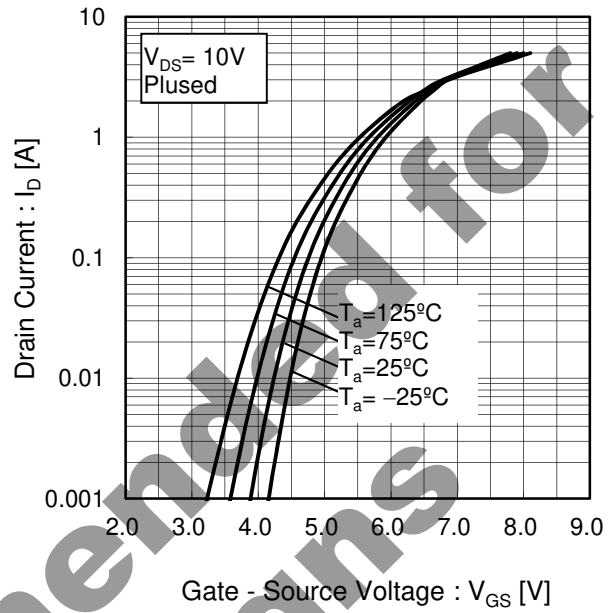
Fig.12 Typical Transfer Characteristics

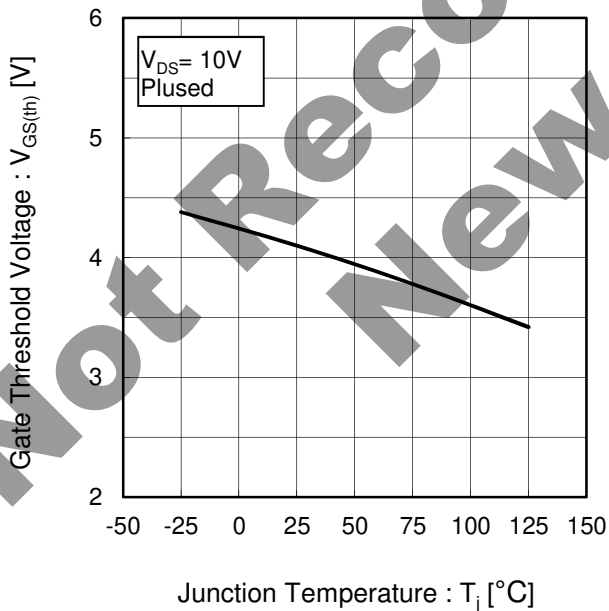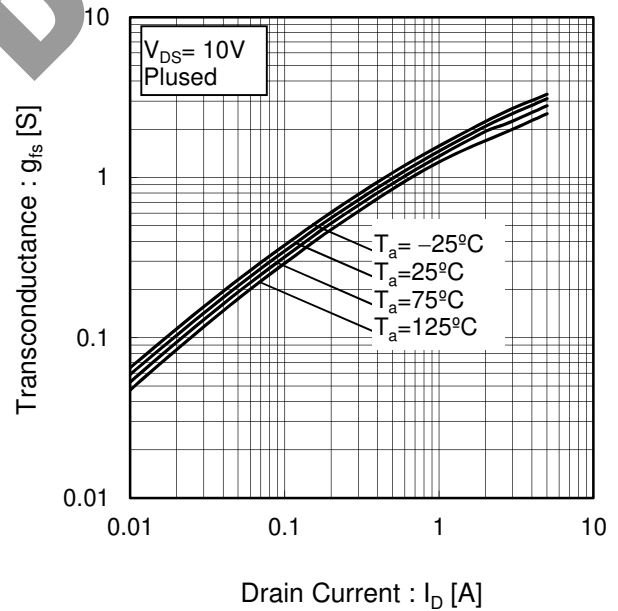Fig.13 Gate Threshold Voltage
vs. Junction Temperature

Fig.14 Transconductance vs. Drain Current

●Electrical characteristic curves

Fig.15 Static Drain - Source On - State
Resistance vs. Gate Source Voltage
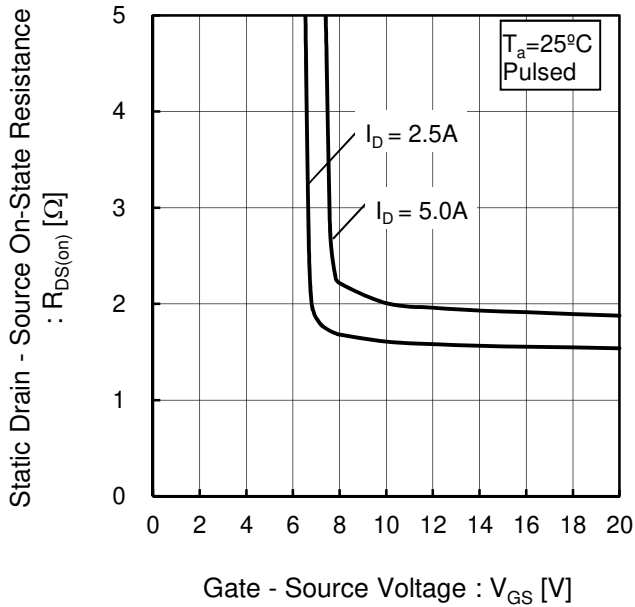

Fig.16 Static Drain - Source On - State
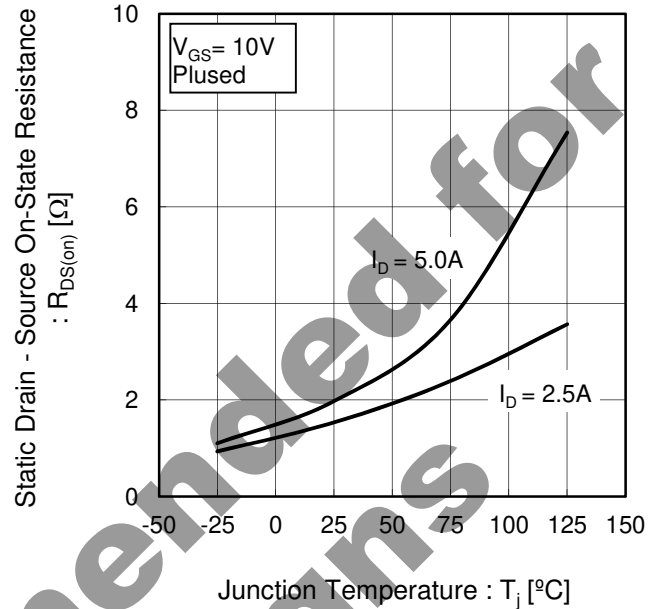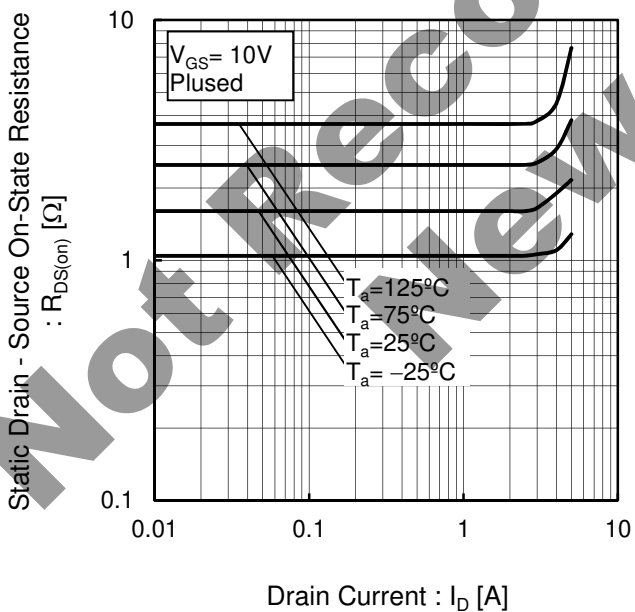Resistance vs. Junction Temperature

Fig.17 Static Drain - Source On - State
Resistance vs. Drain Current

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● **Electrical characteristic curves**

Fig.18 Typical Capacitance
      vs. Drain - Source Voltage

Capacitance : C [pF]

C_{iss}

C_{oss}

C_{rss}

T_a=25ºC
f = 1MHz
V_{GS} = 0V

Drain - Source Voltage : V_{DS} [V]

Fig.19 Coss Stored Energy

Coss Stored Energy : E_{OSS} [uJ]

T_a=25ºC

Drain - Source Voltage : V_{DS} [V]

Fig.20 Switching Characteristics

Switching Time : t [ns]

t_f

$t_{d(off)}$

$t_{d(on)}$

t_r

V_{DD} ≒ 400V
V_{GS} = 10V
R_G= 10Ω
T_a = 25ºC
Pulsed

Drain Current : I_D [A]

Fig.21 Dynamic Input Characteristics

Gate - Source Voltage : V_{GS} [V]

T_a = 25ºC
V_{DD}= 400V
I_D= 5A
Pulsed

Total Gate Charge : Q_g [nC]

●**Electrical characteristic curves**

Fig.22 Inverse Diode Forward Current
vs. Source - Drain Voltage

$V_{GS}=0V$
Pulsed

Inverse Diode Forward Current : I_S [A]

$T_a=125ºC$
$T_a=75ºC$
$T_a=25ºC$
$T_a= -25ºC$

Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time
vs.Inverse Diode Forward Current

$T_a=25ºC$
$V_{GS} = 0V$
di / dt = 100A / μs
Pulsed

Reverse Recovery Time : t_{rr} [ns]

Inverse Diode Forward Current : I_S [A]

● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

Fig.1-2 Switching Waveforms

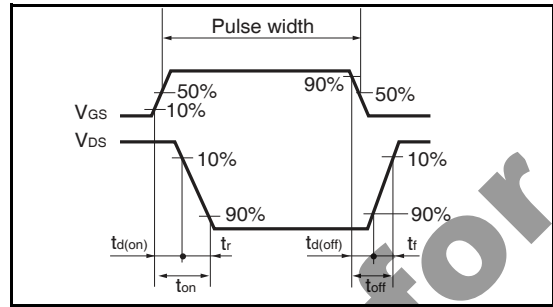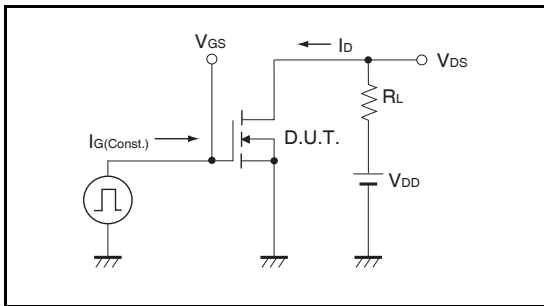### Fig.2-1 Gate Charge Measurement Circuit

Fig.2-2 Gate Charge Waveform

Fig.3-1 Avalanche Measurement Circuit

Fig.3-2 Avalanche Waveform

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \frac{V_{(BR)DSS}}{V_{(BR)DSS} - V_{DD}}$$

Fig.4-1 dv/dt Measurement Circuit

Fig.4-2 dv/dt Waveform

Fig.5-1 di/dt Measurement Circuit

Fig.5-2 di/dt Waveform

● **Dimensions** (Unit : mm)

TO-220FM

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
c	0.70	0.85	0.028	0.033
D	9.90	10.30	0.390	0.406
E	4.40	4.80	0.173	0.189
e	2.54		0.100	
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.110	0.126
L	11.50	12.50	0.453	0.492
p	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
x	–	0.38	–	0.015

Dimension in mm / inches

Notice

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1. Our Products are designed and manufactured for application in ordinary electronic equipments (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment [Note 1], transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSⅢ	CLASSⅡb	CLASSⅢ
CLASSⅣ		CLASSⅢ	

2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
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   - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl_2, H_2S, NH_3, SO_2, and NO_2
   - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
   - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
   - [f] Sealing or coating our Products with resin or other coating materials
   - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
   - [h] Use of the Products in places subject to dew condensation

4. The Products are not subject to radiation-proof design.

5. Please verify and confirm characteristics of the final or mounted products in using the Products.

6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.

7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.

8. Confirm that operation temperature is within the specified range described in the product specification.

9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.

2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.

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Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of Ionizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
   [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
   [b] the temperature or humidity exceeds those recommended by ROHM
   [c] the Products are exposed to direct sunshine or condensation
   [d] the Products are exposed to high Electrostatic

2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.

3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.

4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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